

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A floating gate having improved coupling ratio, comprising:

a semiconductor substrate;
a tunneling dielectric layer formed on the semiconductor substrate;
a ~~conductive~~ polycide layer, formed on the tunneling dielectric layer; and
a plurality of ~~conductive~~ polycide spacers, formed on the sidewalls of the ~~conductive~~ polycide layer, and the tops of the ~~conductive~~ polycide spacers level with the surface of the ~~conductive~~ polycide layer, with the ~~conductive~~ polycide spacers and the ~~conductive~~ polycide layer forming the floating gate.

2. (Original) The floating gate as claimed in claim 1, further comprising two neighboring shallow trench isolation structures, and the tunneling dielectric layer located between the two shallow trench isolation structures.

3-4. (Cancelled)

5. (Original) The floating gate as claimed in claim 1, wherein the tunneling dielectric layer is oxide or oxynitride.

6. (Cancelled)

7. (Currently Amended) A floating gate having improved coupling ratio, comprising:

a semiconductor substrate;
a tunneling dielectric layer formed on the semiconductor substrate;
a ~~conductive~~ polycide layer, formed on the tunneling dielectric layer;
a pair of shallow trench isolation formed oppositely adjacent to the ~~conductive~~ polycide layer, wherein the shallow trench isolation is lower than the top surface of the ~~conducting~~ polycide layer; and

a plurality of ~~conductive~~ polycide spacers, formed on the sidewalls of the ~~conductive~~ polycide layer and overlying the shallow trench isolation, and the tops of the ~~conductive~~ polycide spacers level with the surface of the ~~conductive~~ polycide layer, with the ~~conductive~~ polycide spacers and the ~~conductive~~ polycide layer forming the floating gate.

8-9. (Cancelled)

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10. (Original) The floating gate as claimed in claim 7, wherein the tunneling dielectric layer is oxide or oxynitride.

11. (Original) The floating gate as claimed in claim 7, wherein the shallow trench isolation is an oxide layer.